/ Descriptions

DFN1006-2L ESD

DFN1006-2L Plastic Package ESD Protection Diode.

/ Features

1ns 30KV IEC61000-4-2 4 ESD AEC-Q101

Ultra small package, Response Time is Typically < 1 ns, ESD > 30 kV per Human Body Model,IEC61000−4−2 Level 4 ESD Protection, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

MP3

Suitable for cellular phones audio,MP3 players, Digital cameras, Portable devices, mobile telephone and other users, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Peak pulse power (t_p = 8/20μs)	P_K	69	W
Peak pulse current (t_p = 8/20μs)	I_{PP}	5.5	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±30	KV
ESD according to IEC61000-4-2 contact discharge		±30	
Junction temperature	T_J	150	
Storage temperature	T_{STG}	-55~+150	

/ Electrical Characteristics(Ta=25)

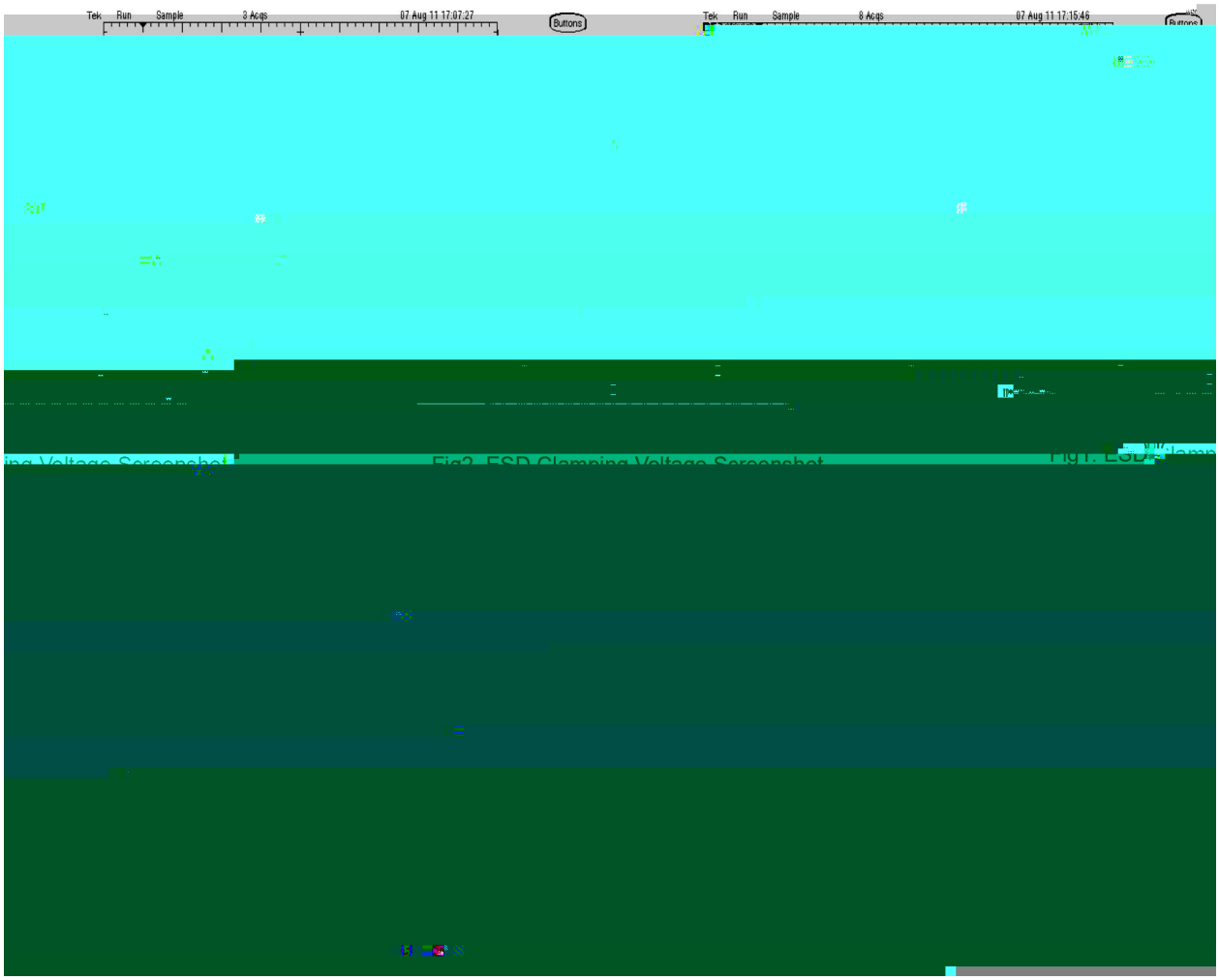
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse maximum working voltage	V_{RWM}				3.3	V
Reverse leakage current	I_R	V_{RWM} = ± 3.3V			± 0.1	uA
Reverse breakdown voltage[1)]	V_{BR}	I_T = 1mA	5.0		6.8	V
Clamping voltage [2)]	V_C	I_{PP} = 1A t_p = 8/20μs			9.8	V
		I_{PP} = 5.5A t_p = 8/20μs			12.5	V
Junction capacitance	C_J	V_R = 0V f = 1MHz			15	pF

Notes:

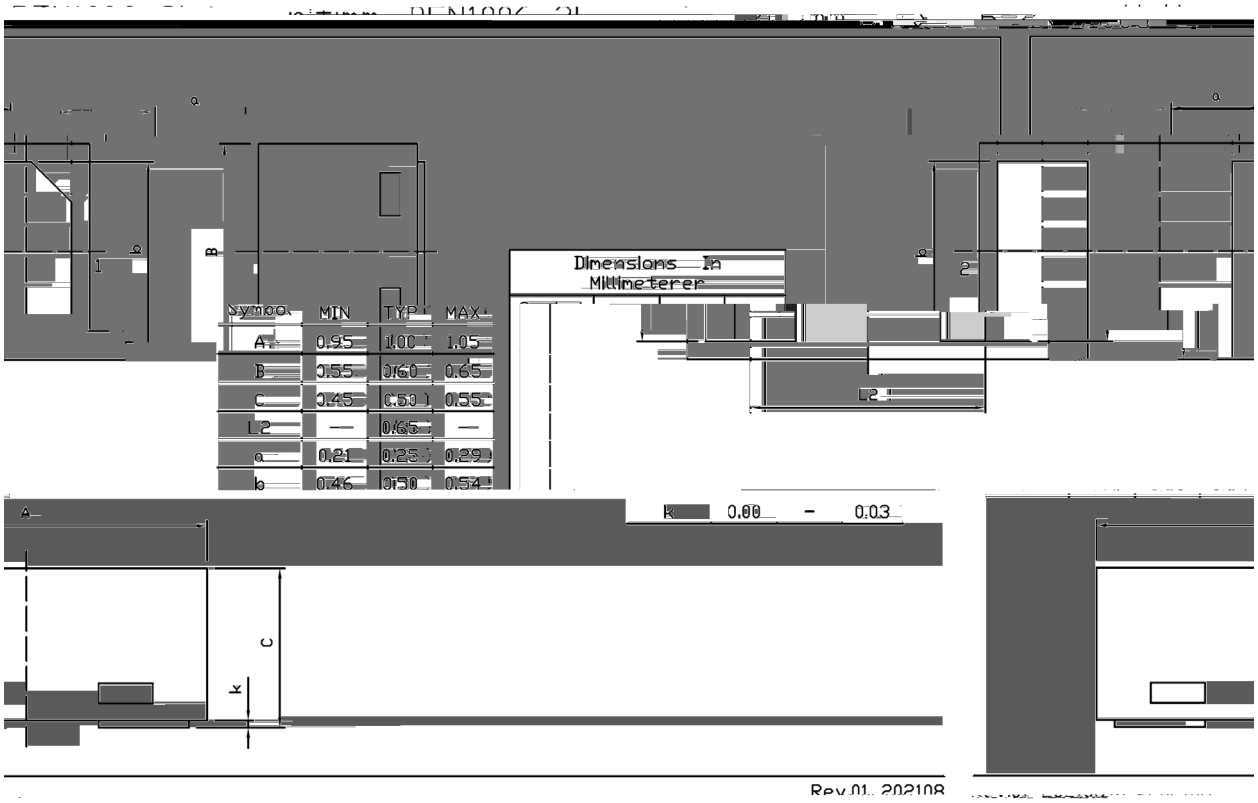
1) V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 .

2) Non-repetitive current pulse, according to IEC61000-4-5.

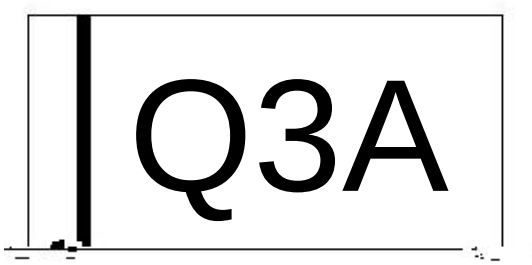
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



Q

3A

Note

Q	Automobile halogen-free product Code
3A	Product Type